

CLAIMS

1. A method for cleaning a semiconductor wafer, including:

supplying a semiconductor wafer whose surface has an oxide film formed thereon with a cleaning solution capable of removing the oxide film; and

cleaning, while rotating, the semiconductor wafer to remove the oxide film formed on the surface of the semiconductor wafer, wherein

the oxide film is removed such that a rotational speed of the semiconductor wafer is 300 rpm or more after the cleaning with the cleaning solution is started and before 80% or more of the oxide film formed on the surface of the semiconductor wafer is removed, and then the rotational speed of the semiconductor wafer is changed to 100 rpm or less to completely remove the oxide film.

2. The method for cleaning a semiconductor wafer according to claim 1, wherein

the semiconductor wafer is a silicon wafer, and the cleaning solution capable of removing the oxide film is hydrofluoric acid.

3. The method for cleaning a semiconductor wafer according to claim 1 or 2, wherein

the oxide film removal at the rotational speed of 300 rpm or more is performed before 90% of the oxide film formed on the surface of the semiconductor wafer is removed, and

then the rotational speed of the semiconductor wafer is changed to 100 rpm or less to completely remove the oxide film.